

## 30V N+P Dual Channel MOSFETs

### General Description

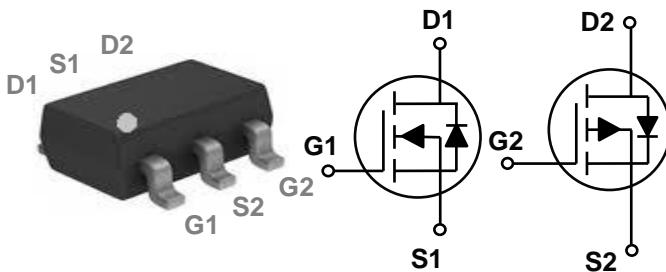
These N+P dual Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
30V	30mΩ	4A
-30V	65mΩ	-3A

### Features

- Fast switching
- Green Device Available
- Suit for 4.5V Gate Drive Applications

### SOT-23-6 DualPin Configuration



### Applications

- DC Fan
- Motor Drive Applications
- Networking
- Half / Full Bridge Topology

### Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating		Units
V <sub>DS</sub>	Drain-Source Voltage	30	-30	V
V <sub>GS</sub>	Gate-Source Voltage	±20	±20	V
I <sub>D</sub>	Drain Current – Continuous (T <sub>C</sub> =25°C)	4	-3	A
	Drain Current – Continuous (T <sub>C</sub> =100°C)	2.5	-1.8	A
I <sub>DM</sub>	Drain Current – Pulsed <sup>1</sup>	16	-12	A
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> =25°C)	2		W
	Power Dissipation – Derate above 25°C	0.016		W/°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 150		°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150		°C

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction to ambient	---	100	°C/W



# FTK3714NP

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N-CH Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise)

### Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=30V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu A$
		$V_{DS}=24V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	10	$\mu A$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA

### On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=4A$	---	22	30	m $\Omega$
		$V_{GS}=4.5V, I_D=2A$	---	35	46	m $\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.6	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4	---	mV/ $^\circ\text{C}$
$g_{fs}$	Forward Transconductance	$V_{DS}=10V, I_D=3A$	---	6.5	---	S

### Dynamic and switching Characteristics

$Q_g$	Total Gate Charge <sup>3, 4</sup>	$V_{DS}=15V, V_{GS}=4.5V, I_D=6A$	---	4.1	8	nC
$Q_{gs}$	Gate-Source Charge <sup>3, 4</sup>		---	1	2	
$Q_{gd}$	Gate-Drain Charge <sup>3, 4</sup>		---	2.1	4	
$T_{d(on)}$	Turn-On Delay Time <sup>3, 4</sup>	$V_{DD}=15V, V_{GS}=10V, R_G=6\Omega$ $I_D=1A$	---	2.8	5	ns
$T_r$	Rise Time <sup>3, 4</sup>		---	7.2	14	
$T_{d(off)}$	Turn-Off Delay Time <sup>3, 4</sup>		---	15.8	30	
$T_f$	Fall Time <sup>3, 4</sup>		---	4.6	9	
$C_{iss}$	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, F=1\text{MHz}$	---	345	500	pF
$C_{oss}$	Output Capacitance		---	55	80	
$C_{rss}$	Reverse Transfer Capacitance		---	32	45	
$R_g$	Gate resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	---	3.2	6.4	$\Omega$

### Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current	$V_G=V_D=0V, \text{Force Current}$	---	---	4	A
$I_{SM}$	Pulsed Source Current		---	---	8	A
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$ .
3. Essentially independent of operating temperature.



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## 30V N+P Dual Channel MOSFETs

P-CH Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise)

### Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	$BV_{DSS}$ Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=-1\text{mA}$	---	-0.03	---	V/ $^\circ\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-30V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	$\mu\text{A}$
		$V_{DS}=-24V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	-10	$\mu\text{A}$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA

### On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-3A$	---	45	65	m $\Omega$
		$V_{GS}=-4.5V, I_D=-2A$	---	65	90	m $\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	-1.6	-2.2	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4	---	mV/ $^\circ\text{C}$
gfs	Forward Transconductance	$V_{DS}=-10V, I_D=-3A$	---	3.7	---	S

### Dynamic and switching Characteristics

$Q_g$	Total Gate Charge <sup>2,3</sup>	$V_{DS}=-30V, V_{GS}=-4.5V, I_D=-2A$	---	5	8	nC
$Q_{gs}$	Gate-Source Charge <sup>2,3</sup>		---	1.4	3	
$Q_{gd}$	Gate-Drain Charge <sup>2,3</sup>		---	1.7	4	
$T_{d(on)}$	Turn-On Delay Time <sup>2,3</sup>	$V_{DD}=-30V, V_{GS}=-10V, R_G=6\Omega$ $I_D=-1A$	---	3.4	6	ns
$T_r$	Rise Time <sup>2,3</sup>		---	10.8	21	
$T_{d(off)}$	Turn-Off Delay Time <sup>2,3</sup>		---	26.9	51	
$T_f$	Fall Time <sup>2,3</sup>		---	6.9	13	
$C_{iss}$	Input Capacitance	$V_{DS}=-30V, V_{GS}=0V, F=1\text{MHz}$	---	420	810	pF
$C_{oss}$	Output Capacitance		---	50	80	
$C_{rss}$	Reverse Transfer Capacitance		---	35	60	

### Drain-Source Diode Characteristics and Maximum Ratings

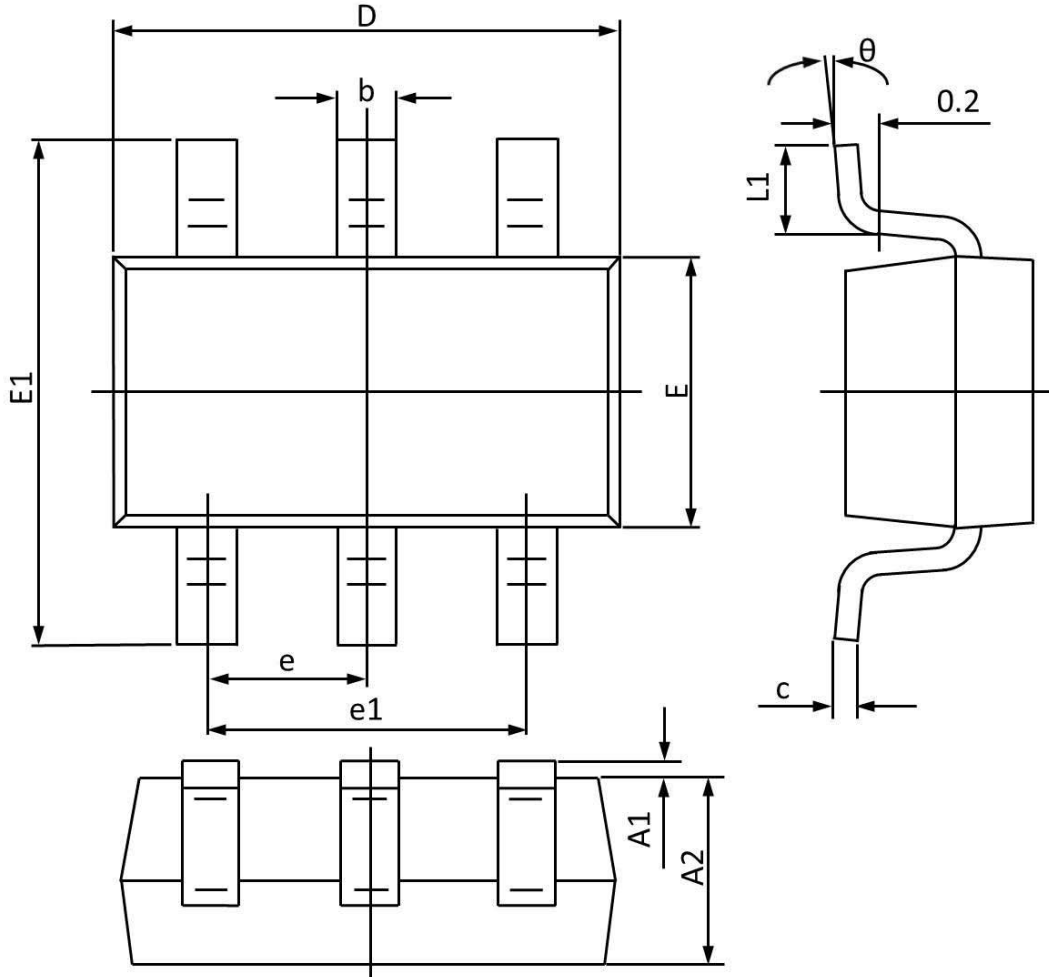
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current	$V_G=V_D=0V$ , Force Current	---	---	-3	A
$I_{SM}$	Pulsed Source Current		---	---	-6	A
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1	V

Note :

4. Repetitive Rating : Pulsed width limited by maximum junction temperature.
5. The data tested by pulsed, pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .
6. Essentially independent of operating temperature.

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### SOT-23-6 Dual PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A1	0.000	0.100	0.000	0.004
A2	1.000	1.200	0.040	0.047
b	0.300	0.500	0.012	0.019
c	0.047	0.207	0.002	0.008
D	2.800	3.000	0.110	0.118
E	1.500	1.800	0.059	0.070
E1	2.600	3.000	0.103	0.118
e	0.950 TYP		0.037 TYP	
e1	1.900 TYP		0.075 TYP	
L1	0.250	0.550	0.010	0.021
θ	0°	8°	0°	8°